





150V PNP HIGH VOLTAGE SWITCHING TRANSISTOR IN SOT89

Features

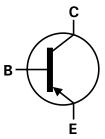
- BV_{CEO} > -150V
- BV_{CEV} > -180V
- I_C = -700mA high Continuous Collector Current
- Low saturation voltage V_{CE(sat)} < -300mV @ -100mA
- Complementary NPN type: FCX495
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

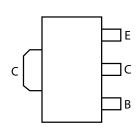
- Case: SOT89
- Case material: molded plastic. "Green" molding compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.052 grams (Approximate)







Device Symbol



Top View Pin Out

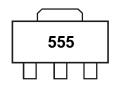
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FCX555TA	555	7	12	1.000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



555 = Product Type Marking Code





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Limit	Unit
Collector-Base Voltage	V _{CBO}	-180	V
Collector-Emitter Voltage	V _{CEV}	-180	V
Collector-Emitter Voltage	V _{CEO}	-150	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-0.7	Α
Peak Pulse Current	I _{CM}	-2	А

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		1		
Power Dissipation	(Note 6)	P_{D}	1.5	W	
	(Note 7)		2.1		
	(Note 5)		125		
Thermal Resistance, Junction to Ambient Air	(Note 6)	Roja	83	°C/W	
	(Note 7)		60		
Thermal Resistance, Junction to Lead	(Note 8)	ReJL	10.01	°C/W	
Operating and Storage Temperature Range		T _J , T _{STG}	-65 to +150	°C	

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	≥ 4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

Notes:

- 5. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

 6. Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.

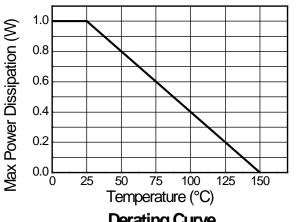
 7. Same as note (5), except the device is mounted on 50mm x 50mm 1oz copper.

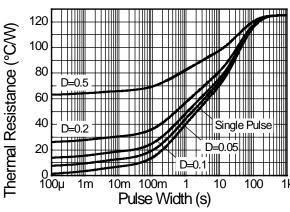
 8. Thermal resistance from junction to solder-point (on the exposed collector pad).

 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



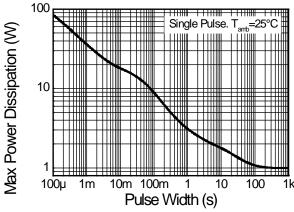
Thermal Characteristics and Derating Information





Derating Curve

Transient Thermal Impedance



Pulse Power Dissipation





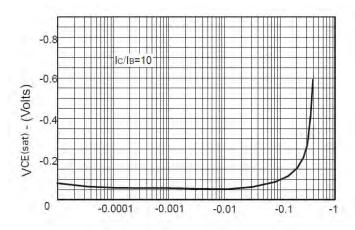
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-180	_	_	V	I _C = -100μA
Collector-Emitter Breakdown Voltage	BV _{CEV}	-180	_	_	V	$I_C = -1\mu A$, $-0.3V < V_{BE} < 1V$
Collector-Emitter Breakdown Voltage	BV _{CER}	-180	_	_	V	$I_C = -1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-150	_	_	V	I _C = -1mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8.1	_	V	I _E = -100μA
Collector Cutoff Current	l	_	<1	-20	nA	V _{CB} = -144V
Collector Catori Carrent	I _{CBO}	ı	-	-10	μΑ	$V_{CB} = -144V, T_A = +100^{\circ}C$
Emitter Cutoff Current	I _{EBO}	_	<1	-20	nA	V _{EB} = -6V
DC current transfer Static ratio (Note 10)	h	100		_		$I_C = -10 \text{mA}, V_{CE} = -5 \text{V}$
De current transfer Static ratio (Note 10)	h _{FE}	100		300		$I_C = -100 \text{mA}, V_{CE} = -5 \text{V}$
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}	_	_	-300	mV	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$
Concetor Emitter Saturation Voltage (Note 10)	V CE(sat)	_	_	-400	111 V	$I_C = -250 \text{mA}, I_B = -25 \text{mA}$
Base-Emitter Saturation Voltage (Note 10)	$V_{BE(sat)}$	1	_	-1000	mV	$I_C = -250 \text{mA}, I_B = -25 \text{mA}$
Base-Emitter Turn-on Voltage (Note 10)	V _{BE(on)}	_	_	-950	mV	$I_C = -250 \text{mA}, V_{CE} = -5 \text{V}$
Transitional Frequency	f⊤	_	100	_	MHz	I _E = -50mA, V _{CE} = -10V
						f = 100MHz
Output capacitance	C_{obo}	_	_	10	pF	V _{CB} = -10V, f = 1MHz,

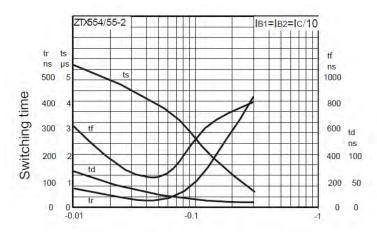
Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

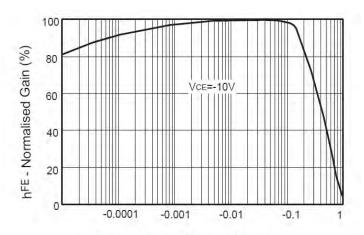


Ic - Collector Current (Amps)



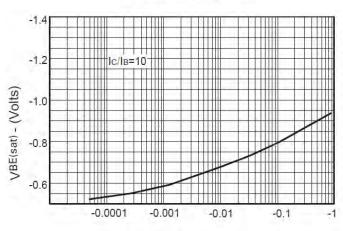
Ic - Collector Current (Amps)

VCE(sat) v IC



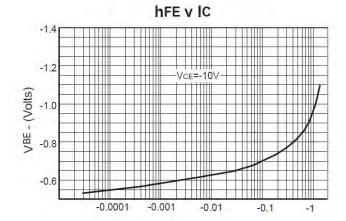
Ic - Collector Current (Amps)

Switching Speeds



Ic - Collector Current (Amps)

VBE(sat) v IC



Ic - Collector Current (Amps)

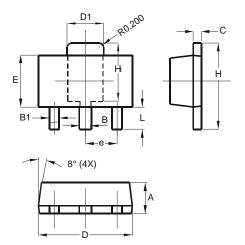
VBE(on) v IC





Package Outline Dimensions

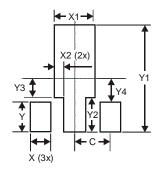
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT89				
Dim	Min	Max		
Α	1.40	1.60		
В	0.44	0.62		
B1	0.35	0.54		
C	0.35	0.44		
D	4.40	4.60		
D1	1.62	1.83		
Е	2.29	2.60		
е	1.50 Typ			
Н	3.94	4.25		
H1	2.63	2.93		
L	0.89 1.20			
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Х	0.900
X1	1.733
X2	0.416
Y	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
С	1.500

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to voltage spacing between terminals.





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